MICROWAVE SEMICONDUCTOR
TECHNICAL DATA

POWER GaAs MMIC

TMD0507-2

Features:

- HIGH POWER
  P_{1dB}= 33 dBm at 5.1 to 7.2 GHz
- HIGH GAIN
  G_{1dB}= 22 dB at 5.1 to 7.2 GHz
- BROAD BAND INTERNALLY MATCHED
- HERMETICALLY SEALED PACKAGE

ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

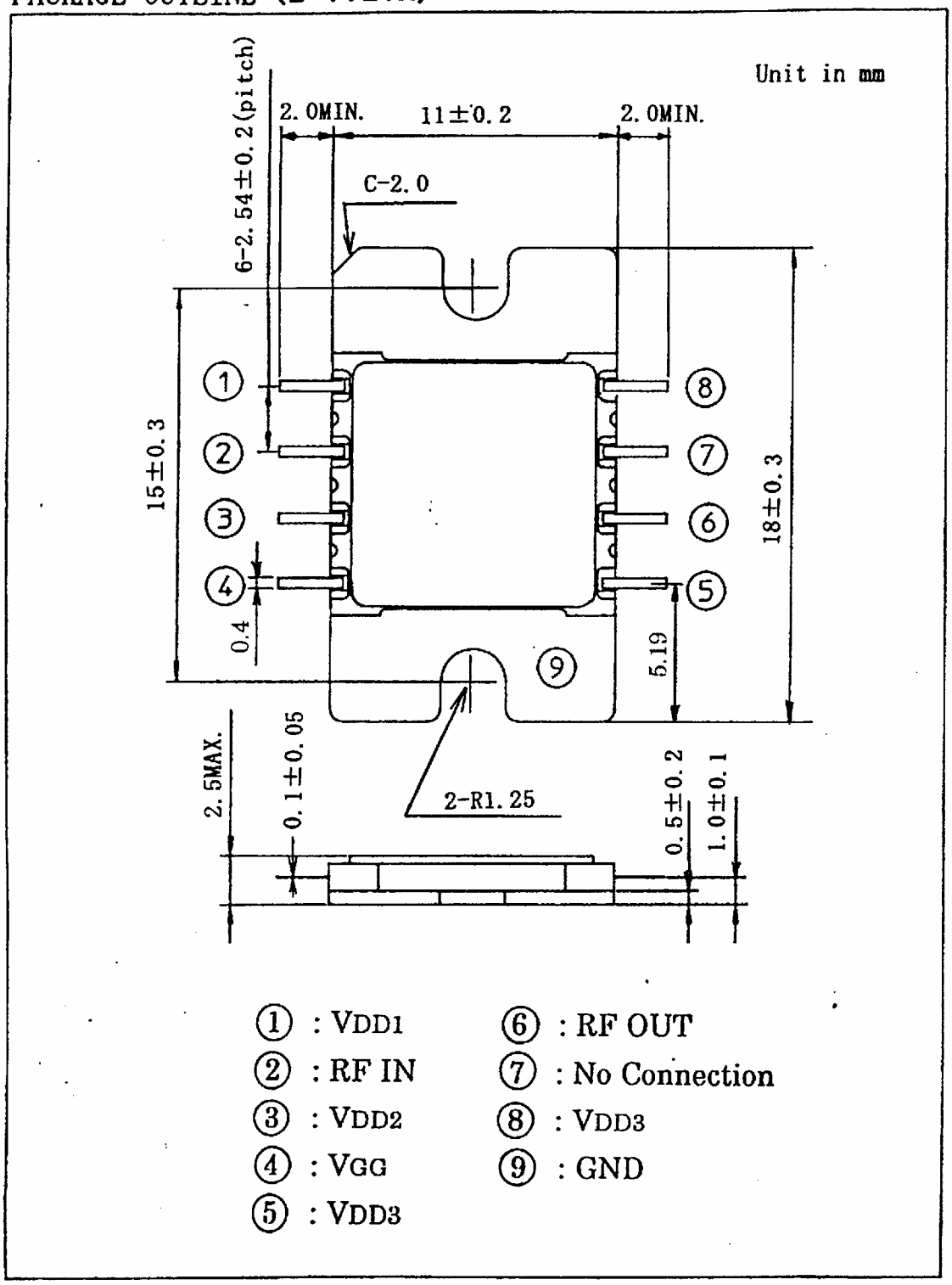
CHARACTERISTICS	SYMBOL	UNIT	RATINGS
DRAIN SUPPLY VOLTAGE	V_{DD}	V	15
GATE SUPPLY VOLTAGE	V_{GG}	V	-10
INPUT POWER	Pin	W	0.1
FLANGE TEMPERATURE	Tf	℃	-30～+80
STORAGE TEMPERATURE	Tstg	℃	-65～+175

RF CHARACTERISTICS (Ta=25℃)

CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Output Power at 1 dB Gain Compression Point	P_{1dB}	$V_{DD1}=V_{DD2}=V_{DD3}$= 10V, V_{GG}=-5 V f= 5.1-7.2 GHz	dBm	32.0	33.0	—
Power Gain at 1 dB Gain Compression Point	G_{1dB}		dB	20.0	22.0	—
Drain Current	I_{DD} *		A	—	1.70	2.00
Input VSWR	VSWRi		—	—	—	3.0

* $I_{DD}=I_{DD1}+I_{DD2}+I_{DD3}$

PACKAGE OUTLINE (2-11E1A)



HANDLING PRECAUTIONS FOR PACKAGED TYPE

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260℃. Flanges of devices should be attached using screws and washers. Recommended torques are 0.18-0.20 N·m.